

Quad 2-input NOR gates with LSTTL compatible inputs in bare die form

Rev 1.0 18/05/21

Description

The 74ACT02 quad 2-input NOR gate is fabricated on a 1.5µm advanced CMOS process combining high speed LSTTL performance with CMOS low power. The device performs the Boolean function Y = (A + B) or Y = $\overline{A} \cdot \overline{B}$ in positive logic. Internal circuitry comprises of three stages and includes buffered output for high noise immunity and stability. Inputs are directly compatible with LSTTL outputs. All inputs are protected against ESD and excess voltage transients.

Features:

- Inputs directly accept TTL
- Outputs directly interface CMQS NMOS and TTL
- Outputs Source/Sink 24 m/
- Low Input Current: 1µX
- Functionally compatible with bipolar 74LS02
- Lower power afternative to bipolar logic

Ordering Information

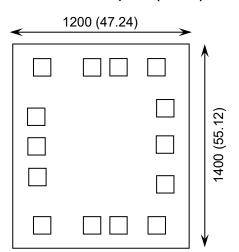
The following part suffixes apply:

No suffix - MIL-STD-883 /2010B Visual Inspection.

For High Reliability versions of this product viscose see

54ACT02

Die Dimensions in µm (mils)



Supply Formats:

- Defaut Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 350µm(14 Mils) On request
- Assembled into Ceramic Package On request

Mechanical Specification

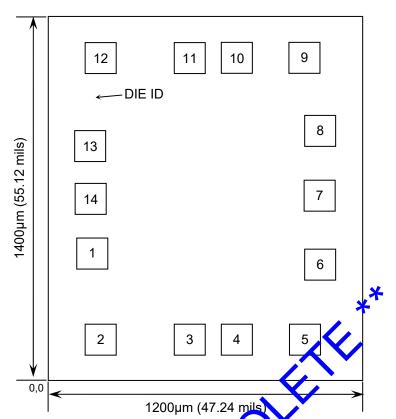
Die Size (Unsawn)	1200 x 1400	μm
(5.1.5.1.1.7)	47 x 55	mils
Minimum Bond Pad Size	130 x 130	μm
Willimani Bond Pad Size	5.12 x 5.12	mils
Die Thielmese	350 (±20)	μm
Die Thickness	13.78 (±0.79)	mils
Top Metal Composition	Al 1%Si 1.1μ	m
Back Metal Composition	N/A – Bare S	Si





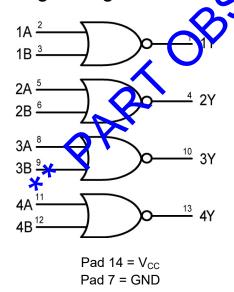
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Pad Layout and Functions



		COORDINA	ATES (mm)
PAD	FUNCTION		` ,
		X	Y
1	1Y	0.100	0.430
2	1A	0.140	0.100
3	1B	0.480	0.100
4	2	0.660	0.100
5	2A	0.920	0.100
6	2B	0.980	0.380
	GND	0.980	0.650
8	3A	0.980	0.900
9	3B	0.920	1.180
10	3Y	0.660	1.180
11	4A	0.480	1.180
12	4B	0.140	1.180
13	4Y	0.100	0.840
14	V _{CC}	0.140	0.640
CON	INECT CHIP BA	CK TO V _{CC} O	R FLOAT

Logic Diagram



Truth Table

INP	JTS	OUTPUT			
Α	В	Υ			
L	L	Н			
L	Н	L			
Н	L	L			
Н	Н	L			
H = High level (steady state)					
I = I	ow leve	l (steady state)			





Absolute Maximum Ratings¹

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PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage (Referenced to GND)	V _{CC}	-0.5 to +7.0	V
DC Input Voltage (Referenced to GND)	V _{IN}	-0.5 to V _{CC} +0.5	V
DC Output Voltage (Referenced to GND)	V _{OUT}	-0.5 to V _{CC} +0.5	V
DC Input Current	I _{IN}	±20	mA
DC Output Current, per pad	I _{OUT}	±50	mA
DC Supply Current, V _{CC} or GND, per pad	I _{cc}	±50	mA
Power Dissipation in Still Air ²	P _D	750	mW
Storage Temperature Range	T _{STG}	-65 to 150	°C

^{1.} Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Measured in plastic DIP package, results in die form are dependent on die attach and assembly method.

Recommended Operating Conditions³ (Voltages Referenced to GND)

			`		,
PARAMETE	SYMBOL	MIN	MAX	UNITS	
DC Supply Voltage	V _{CC}	4.5	5.5	V	
DC Input or Output Voltage	Э	V_{IN} , V_{OUT}	* 0	V _{CC}	V
Operating Temperature Ra	TJ	* -40	+85	°C	
Output current - High	I _{OH}	_	-24	mA	
Output current - Low			-	24	mA
Input Rise or Fall rate	V _{CC} = 4.5V	ΔΨΔΥ	0	10	ns/V
(V _{IN} from 0.8V to 2V)	$V_{CC} = 5.5V$	ΔIΔV	0	8	115/ V

^{3.} This device contains protection circuitry to guard equals t damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than naximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range GND \leq (V_{IN} or V_{OUT}). V_{CC} Urused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC Electrical Characteristics (Voltages referenced to GND)

PARAMETER	SMBOL	V _{cc}	CONDITIONS	LIMITS			UNITS
	O MILDS L	▼CC	CONDITIONS	25°C	85°C	FULL RANGE⁴	Oitilo
Minimum High-Level	V	4.5V	$V_{OUT} = 0.1V$	2	2	2	V
Input Voltage	5.5V	or V _{CC} -0.1V	2	2	2	V	
Maximum Low-Lovel	V _{IL}	4.5V	$V_{OUT} = 0.1V$	0.8	8.0	0.8	V
Input volage	V IL	5.5V	or V _{CC} -0.1V	0.8	8.0	0.8	v
<u> </u>		4.5V	Ι _{ΟυΤ} = 50μΑ	0.1	0.1	0.1	V
**		5.5V	1001 – 30μΑ	0.1	0.1	0.1	V
Minimum Low-Level	V _{OL}	4.5V	$V_{IN} = V_{IL} \text{ or } V_{IH}^5$	0.36	0.44	0.44	V
Output Voltage	VOL	5.5V	$I_{OL} = 24mA$	0.36	0.44	0.44	V
	4.5V	$V_{IN} = V_{IL} \text{ or } V_{IH}^{5,6}$	-	-	1.65	V	
	5.5V	$I_{OL} = 75 \text{mA}$	-	-	1.65	\ \ \ \	

^{4. -40°}C ≤ T_J ≤ +85°C 5. All outputs loaded; thresholds on input associated with output under test. 6. Test time 1sec max, measurement made by forcing indicated current and measuring voltage to minimize power dissipation. Test verifies a minimum 75 Ω transmission-line drive capability at 85°C





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DC Electrical Characteristics Continued (Voltages referenced to GND)

PARAMETER	SYMBOL	Vac	V _{cc} CONDITIONS	LIMITS			UNITS
	OTHIBOL	• 66	CONDITIONS	25°C	85°C	FULL RANGE	
Minimum High-Level Output Voltage		4.5V	Ι _{ΟυΤ} = 50μΑ	4.4	4.4	4.4	V
	V _{OH}	5.5V	1001 – 30μΑ	5.4	5.4	5.4	V
	V OH	4.5V	$V_{IN} = V_{IL} \text{ or } V_{IH}^5$	3.86	3.76	3.74	V
		5.5V	$I_{OH} = -24mA$	4.86	4.76	4.76	V
Maximum Input Leakage Current	I _{IN}	5.5V	V _{IN} = V _{CC} or GND	±0.1	±1.0	±1.0	μA
Additional Maximum I _{CC} / Input	ΔI _{CCT}	5.5V	V _{IN} = V _{CC} -2.1V	0.6	1.5	1.5	mA
Minimum Dynamic	I _{OLD}	5.5V	V _{OLD} = 1.65V Max		5	75	mA
Output Current ⁷	I _{OHD}	5.5V	V _{OHD} = 3.85V Min		-75	-75	IIIA
Maximum Quiescent Supply Leakage Current	I _{CC}	5.5V	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0\mu A$	4	40	40	μА

^{7.} Maximum test duration 2ms, one output loaded at a time.

AC Electrical Characteristics⁸ V_{cc} = 6.0V ±0.5V

PARAMETER	SYMBOL	V _{cc}	CONDITIONS		LIMIT	rs	UNITS
17ttVtm=12tt	01111502	100	Colpinono	25°C	85°C	FULL RANGE⁴	00
Maximum Propagation Delay	t _{PLH}	5.0V	C _L = 50pF, Input	8.5	9	9	ns
Input A to Output Y (Figure 1)	t _{PHL}	5.6V	tr = tf =3.0ns	9.5	10	10	110
Maximum Input		5.0V	T _J = 25°C		TYPIC	AL	pF
Capacitance	\bigcirc	0.01	1,5 25 5		4.5		Pi
Power Dissipation	C _{PD}	5.0V	T _J = 25°C,		30		pF
Capacitance	-PD	3.01	C _L = 50pF				P'

^{8.} Not production tested in discorm, characterized by chip design





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Switching Waveform

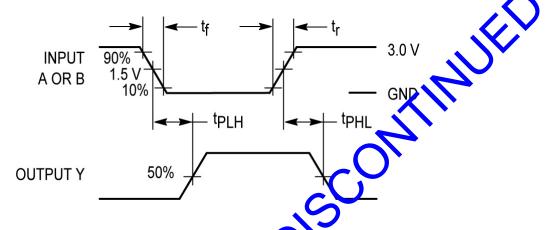
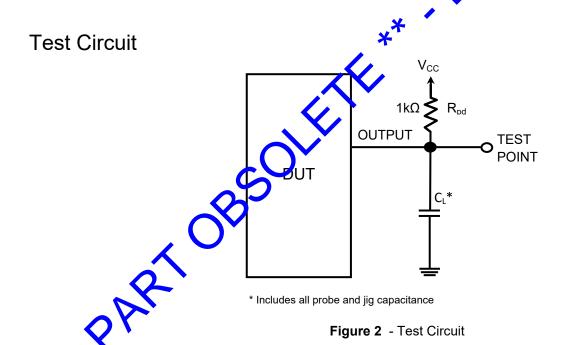


Figure 1 – Propagation delay, Input 4 or B to Output Y



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